



KR 375093B

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TITLE: Method for manufacturing dielectric film

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PATENT-ASSIGNEE: LG PHILIPS LCD CO LTD[GLDS]

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PATENT-FAMILY:

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APPLICATION-DATA:

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ABSTRACTED-PUB-NO: KR2002085258A

BASIC-ABSTRACT:

NOVELTY - A fabrication method of a dielectric film is provided to prevent degradation of the dielectric film and to achieve thermally stable dielectric film by annealing the dielectric film using a laser.

DETAILED DESCRIPTION - A fluorinated amorphous carbon(a-C:F) is deposited on a desired layer. A laser beam is irradiated to the deposited fluorinated amorphous carbon(a-C:F), thereby forming a thermally stable dielectric film without increasing a dielectric constant of the dielectric film. At this time,

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the irradiated laser beam is to be excited only hydrogen contained in the fluorinated amorphous carbon(a-C:F) without exciting fluorine(F). Preferably, the energy of the laser beam is 50-100 mJ/sec and the irradiated time of the laser beam is about 1-10 seconds.

CHOSEN-DRAWING: Dwg.1/10

TITLE-TERMS: METHOD MANUFACTURE DIELECTRIC FILM

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